



PTO/SB/08A (08-03)

Substitute for form 1449A/PTO		<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete If Known</b>		
				Application Number	10/798,547	
Sheet		1	of	2	Filing Date	March 10, 2004
					First Named Inventor	Richard T. Simko
					Art Unit	2818 24
					Examiner Name	Unassigned
					Attorney Docket Number	021343-000700US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code <sup>2</sup> (if known)			
PL	1	US-2003/0112661	06-19-2003	Khalid et al.	
	2	US-6,538,922	03-25-2003	Khalid et al.	
	3	US-5,973,856	10-26-1999	Blyth et al.	
	4	US-5,969,987	10-19-1999	Blyth et al.	
	5	US-5,723,985	03-03-1998	Van Tran et al.	
	6	US-5,294,819	03-15-1994	Simko	
	7	US-5,241,494	08-31-1993	Blyth et al.	
	8	US-5,220,531	06-15-1993	Blyth et al.	
	9	US-5,126,867	06-30-1992	Simko	
	10	US-4,989,179	01-29-1991	Simko	
	11	US-4,890,259	12-26-1989	Simko	
	12	US-4,617,652	10-14-1986	Simko	
	13	US-4,533,846	08-06-1985	Simko	
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	16	US-4,488,060	12-11-1984	Simko	
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	18	US-4,404,475	09-13-1983	Drori et al.	
	19	US-4,393,481	07-12-1983	Owen et al.	
	20	US-4,314,265	02-02-1982	Simko	
V	21	US-4,300,212	11-10-1981	Simko	
	22	US-4,274,012	06-16-1981	Simko	
	23	US-4,263,664	04-21-1981	Owen et al.	
	24	US-4,203,158	05-13-1980	Froiman-Bentchkowsky, et al.	
	25	US-4,119,995	10-10-1978	Simko	
	26	US-4,099,196	07-04-1978	Simko	
	27	US-4,053,349	10-11-1977	Simko	
	28	US-3,996,657	12-14-1976	Simko et al.	
	29	US-3,984,822	10-05-1976	Simko et al.	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code* (if known)				

Examiner Signature	A Ho m. Luu	Date Considered	1/30/05
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Substitute for form 1449B/PTO				<b>Complete If Known</b>	
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				First Named Inventor	Richard T. Simko
				Art Unit	2818 24
				Examiner Name	Unassigned
Sheet	2	of	2	Attorney Docket Number	021343-000700US

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
PL	30	"Fowler-Nordheim Emmission from Texture Surface Features," in <u>Nonvolatile Semiconductor Memory Technology</u> , William D. Brown & Joe E. Brewer eds., IEEE press, p. 163 (1998).	
	31	"MOS Processing," in <u>MOS Integrated Circuits: Theory, Fabrication, Design and Systems Applications of MOS LSI</u> by staff of American Micro Systems Inc., pp. 174-183, (1972).	
	32	BLYTH et al. "Non-Volatile Analog Storage Device Using EEPROM Technology," Digest of Technical Papers 38th IEEE International Solid-State Circuits Conference, pp. 192-315 (1991).	
	33	CHANG et al. "A Low Voltage, Low Power P-Channel EEPROM Cell for Embedded and System-On-A-Chip Applications," Programmable Microelectronics Corp., San Jose, CA (1998).	
	34	DRORI et al. "A Single 5V Supply Nonvolatile Static RAM," Digest of Technical Papers the 1981 IEEE International Solid-State Circuits Conference, pp. 148-149 (1981).	
	35	DRORI et al. "Computer systems acquire both RAM and E <sup>2</sup> Prom from one chip with two memories," Electronic Design 28:91-95 (1980).	
	36	GERBER et al. "Low Voltage Single Supply CMOS Electrically Erasable Read-Only Memory," IEEE Transactions on Electron Devices 27:1211-1216 (1980).	
	37	HARARI et al. "A 256-bit Nonvolatile Static RAM," IEEE International Solid-State Circuits Conference Digest of Technical Papers pp. 108-109 (1978).	
	38	JEWELL-LARSEN et al. "5-VOLT RAM-LIKE TRIPLE POLYSILICON E <sup>2</sup> PROM," IEEE Conference proceedings Second Annual Phoenix Conference on Computers and Communication, pp. 508-511 (1983).	
	39	KLEIN et al. "5-volt-only, nonvolatile RAM owes it all to polysilican," Electronics 52:111-116 (1979).	
PL	40	SALSBURY et al. "High-Performance MOS EPROM's Using a Stacked Gate Cell," Digest of Technical Papers the 1977 IEEE International Solid-State Circuits Conference, pp. 186-187 (1977).	

Examiner Signature	P40 m. luy	Date Considered	1/30/05
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